

Product Summary

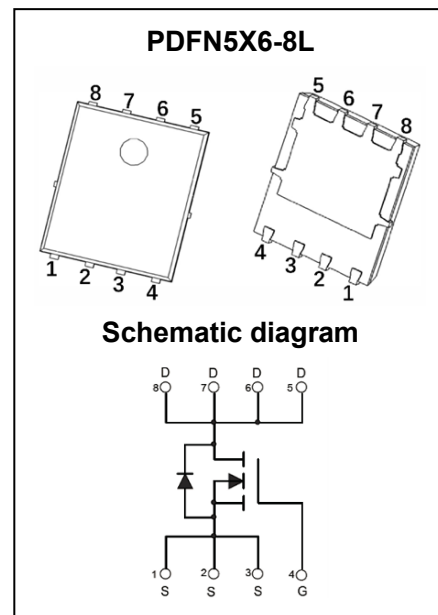
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	6.0m Ω @10V	90A
	7.8m Ω @4.5V	

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Management
- Motor Driving
- High frequency switching, synchronous rectification



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT060N10LNC	PDFN5X6-8L	T060N10L	Reel & Tape	330mm	12mm	5000pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

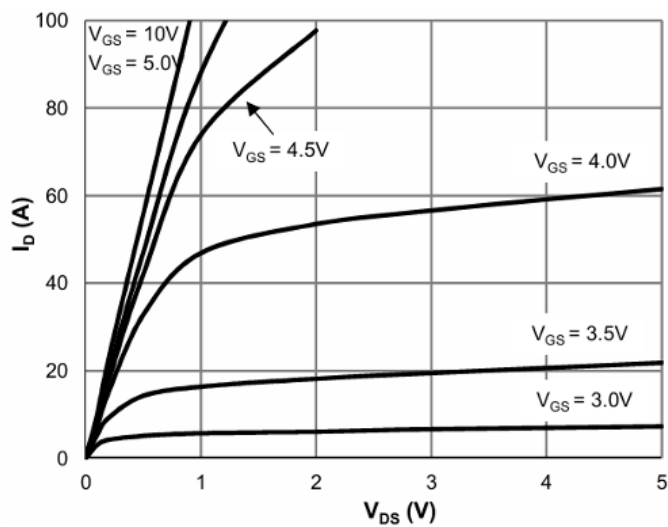
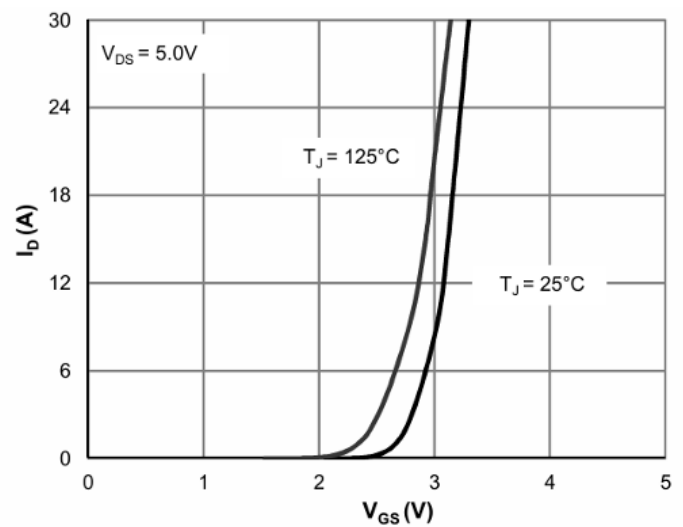
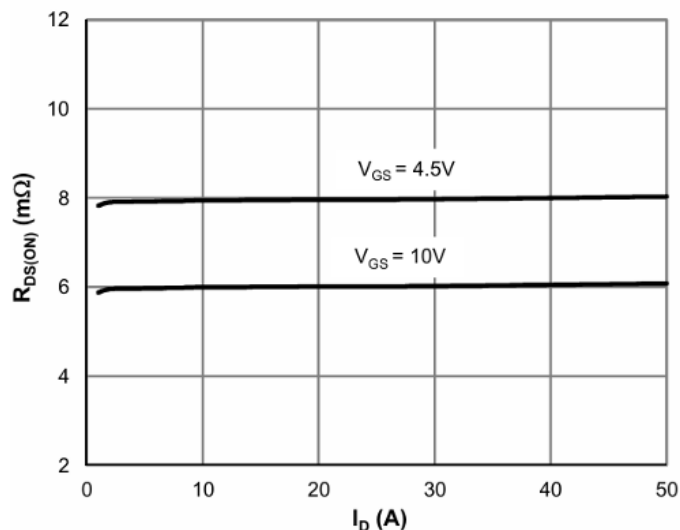
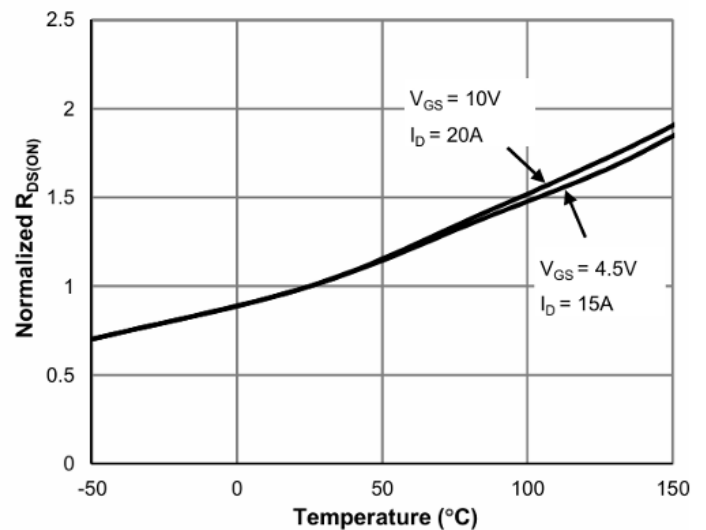
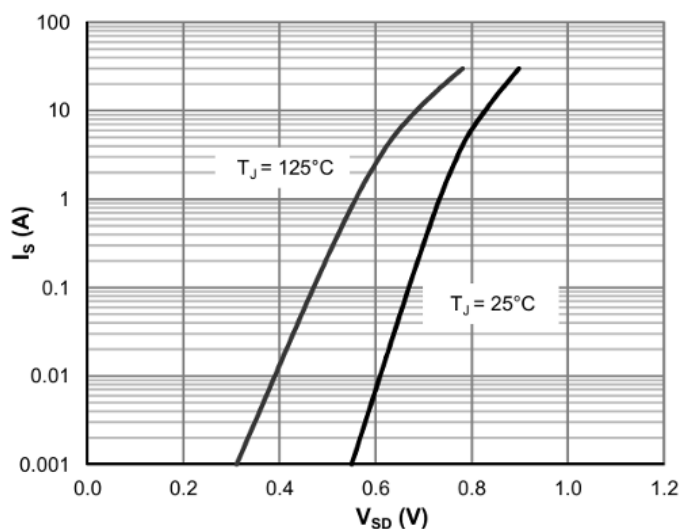
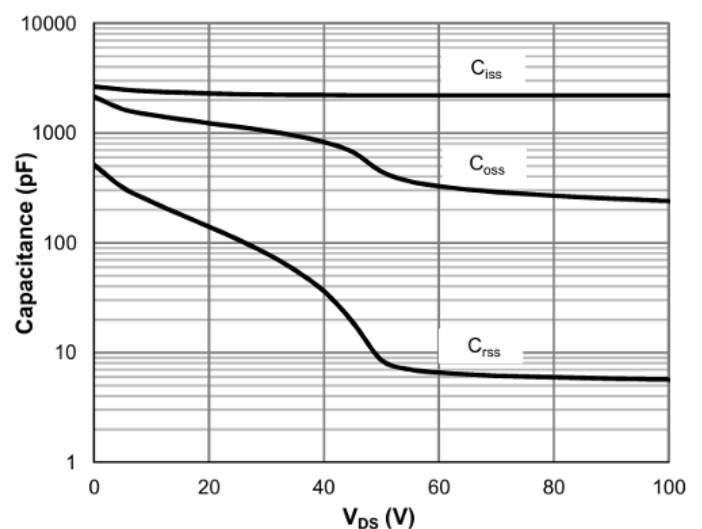
Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current ¹	T _C = 25°C	I _D	90	A
	T _C = 100°C		63	
Pulsed Drain Current ²		I _{DM}	360	A
Single Pulsed Avalanche Current ³		I _{AS}	32	A
Single Pulsed Avalanche Energy ³		E _{AS}	256	mJ
Power Dissipation ⁵	T _C = 25°C	P _D	104	W
Thermal Resistance from Junction to Ambient ⁶		R _{θJA}	50	°C/W
Thermal Resistance from Junction to Case		R _{θJC}	1.0	°C/W
Junction Temperature		T _J	150	°C
Storage Temperature		T _{STG}	-55~ +150	°C

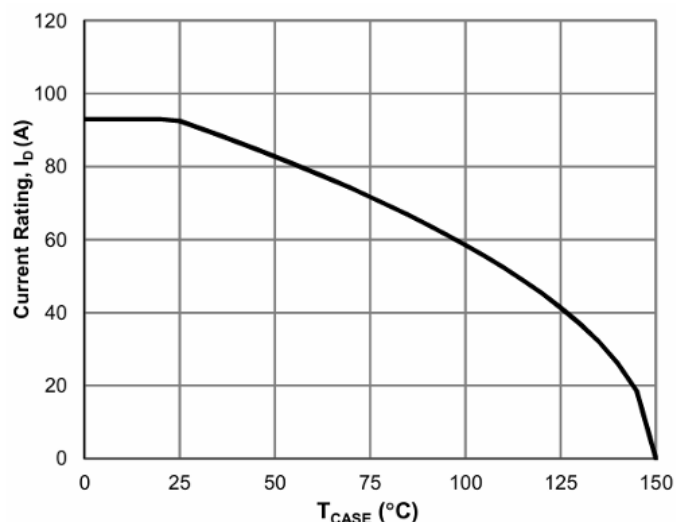
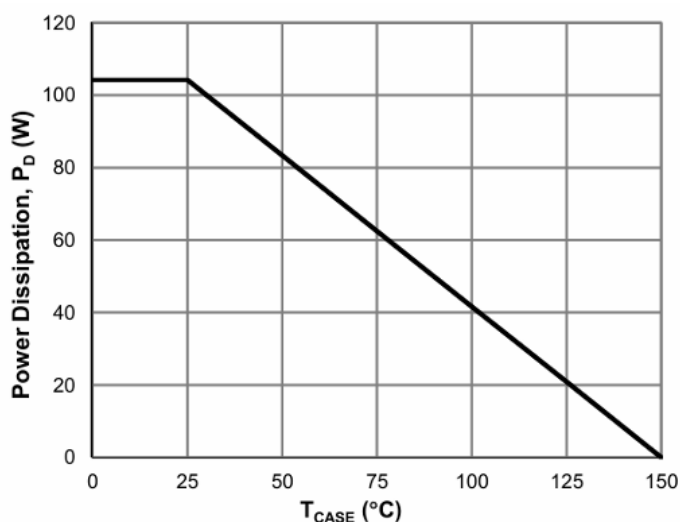
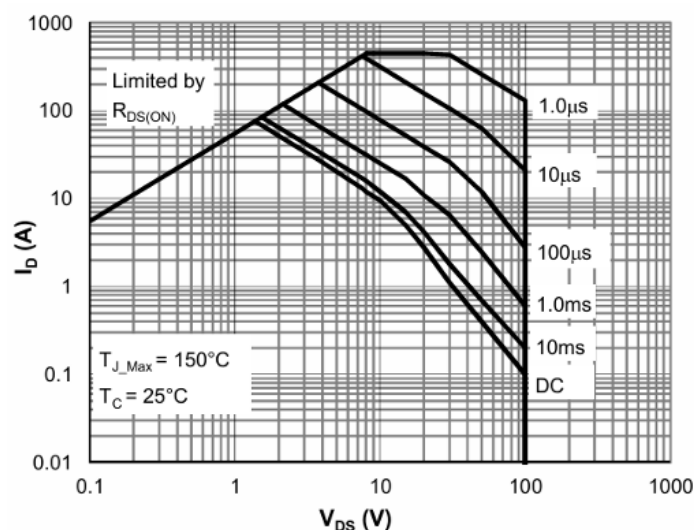
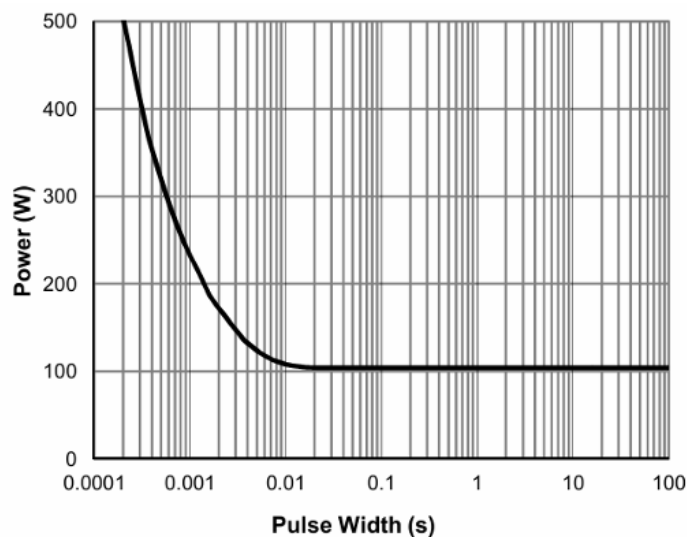
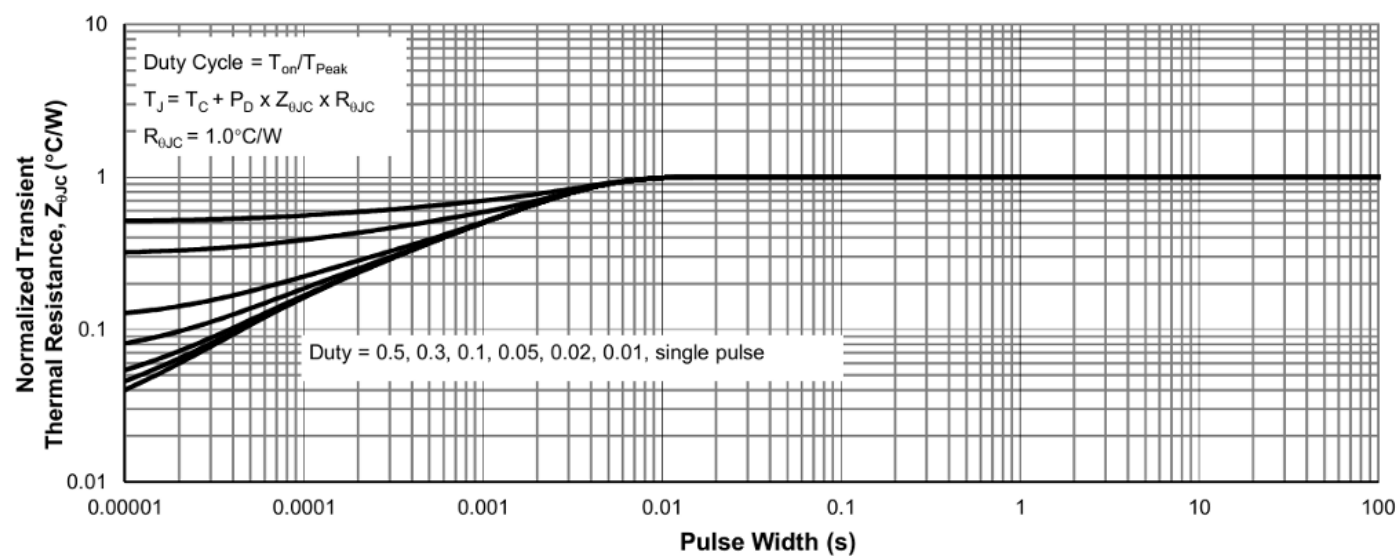
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

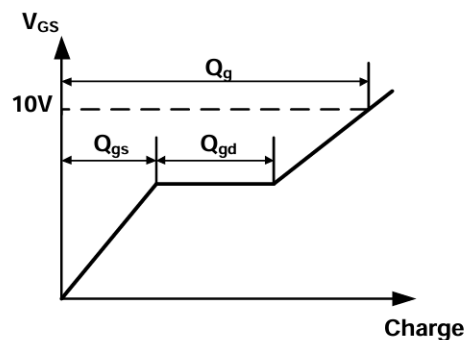
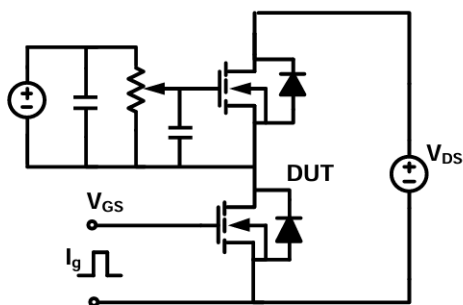
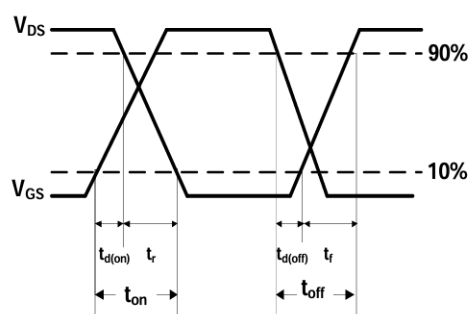
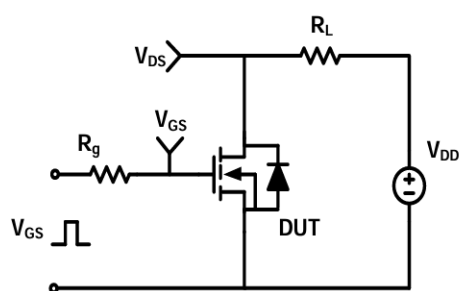
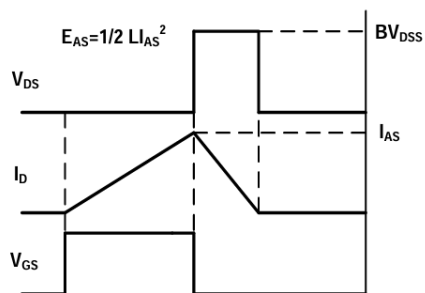
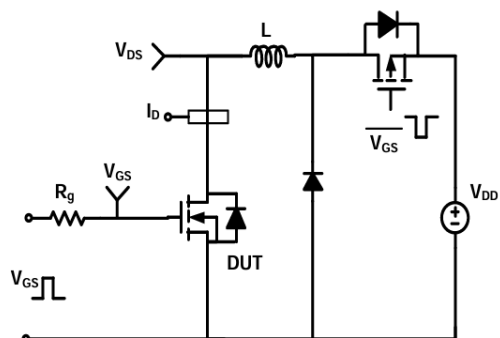
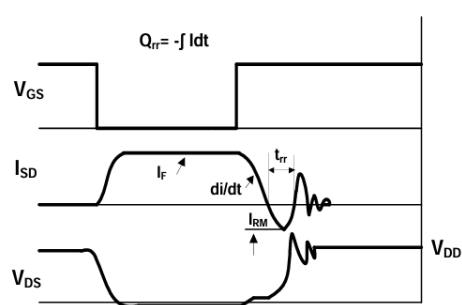
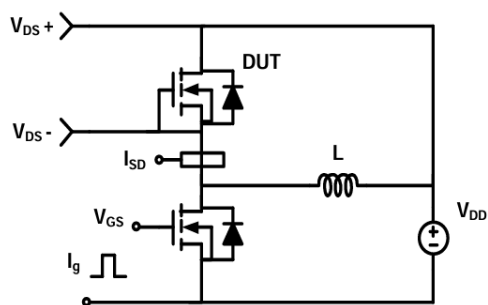
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.7	2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A		6.0	8.0	mΩ
		V _{GS} = 4.5V, I _D = 15A		7.8	10	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iSS}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz		1506		pF
Output Capacitance	C _{oSS}			619		
Reverse Transfer Capacitance	C _{rSS}			7.6		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		1.3		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 20A		31.8		nC
Gate-Source Charge	Q _{gs}			4.0		
Gate-Drain Charge	Q _{gd}			8.2		
Gate Plateau Voltage	V _{plateau}			3.4		V
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50V, V _{GS} = 10V, R _G = 6Ω, R _L = 2.5Ω		10		ns
Turn-On Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(off)}			25		
Turn-Off Fall Time	t _f			20		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 20A			1.2	V
Diode Continuous Forward Current ¹	I _S	T _C = 25℃			90	A
Diode Pulse Forward Current ²	I _{SM}	T _C = 25℃			360	A
Diode Reverse Recovery Time	t _{rr}	I _F = 20A, dI/dt = 100A/μs		50		ns
Diode Reverse Recovery Charge	Q _{rr}	I _F = 20A, dI/dt = 100A/μs		86		nC

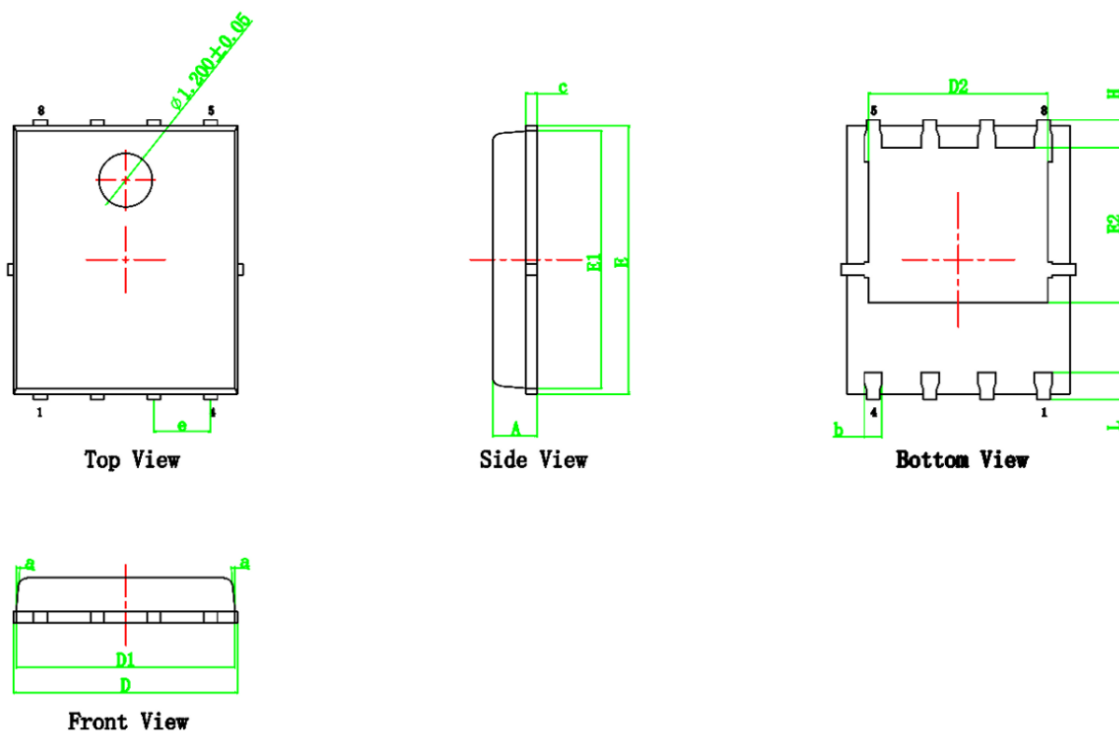
Notes:

- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink.
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Current De-rating

Figure 8: Power De-rating

Figure 9: Maximum Safe Operating

Figure 10: Single Pulse Power Rating, Junction-to-Case

Figure 11: Normalized Maximum Transient Thermal Impedance

Test Circuit
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveform

Diode Recovery Test Circuit & Waveform


PDFN5X6-8L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.200	0.035	0.047
b	0.330	0.510	0.013	0.020
c	0.190	0.300	0.007	0.012
D	4.800	5.220	0.189	0.210
D2	3.900	4.300	0.154	0.170
E	5.900	6.100	0.232	0.240
E1	5.700	5.800	0.224	0.228
E2	3.350	3.750	0.132	0.148
e	1.270REF		0.050REF	
H	0.350	0.720	0.014	0.028
D1	4.800	5.000	0.189	0.197
L	0.350	0.750	0.014	0.030
a	0°	12°	0°	12°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.